

CSD18541F5 60V N 通道 FemtoFET™ MOSFET

1 特性

- 低导通电阻
- 超低 Q_g 和 Q_{gd}
- 超小尺寸
 - 1.53mm x 0.77mm
- 薄型
 - 高度为 0.35mm
- 集成型静电放电 (ESD) 保护二极管
- 无铅且无卤素
- 符合 RoHS 环保标准

2 应用范围

- 针对负载开关应用进行了优化
- 针对通用开关应用进行了优化

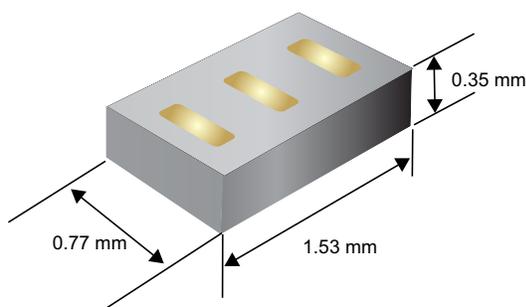
3 说明

这款 54mΩ、60V N 通道 FemtoFET™ MOSFET 技术经过了设计和优化，能够最大限度减小许多空间受限类工业负载开关应用的封装尺寸。这项技术能够在替代标准小信号 MOSFET 的同时大幅减小封装尺寸。

产品概要

$T_A = 25^\circ\text{C}$		典型值	单位
V_{DS}	漏源电压	60	V

典型部件尺寸



产品概要 (接下页)

$T_A = 25^\circ\text{C}$		典型值		单位
Q_g	栅极电荷总量 (10V)	11		nC
Q_{gd}	栅极电荷 (栅极到漏极)	1.6		nC
$R_{DS(on)}$	漏源导通电阻	$V_{GS} = 4.5\text{V}$	57	mΩ
		$V_{GS} = 10\text{V}$	54	
$V_{GS(th)}$	阈值电压	1.75		V

器件信息(1)

器件	数量	包装介质	封装	运输
CSD18541F5	3000	7 英寸卷带	Femto 1.53mm x 0.77mm	卷带
CSD18541F5T	250		SMD 无引线	

(1) 如需了解所有可用封装，请参阅产品说明书末尾的可订购产品附录。

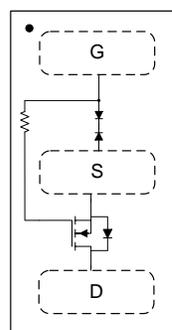
绝对最大额定值

$T_A = 25^\circ\text{C}$		值	单位
V_{DS}	漏源电压	60	V
V_{GS}	栅源电压	± 20	V
I_D	持续漏极电流 ⁽¹⁾	2.2	A
I_{DM}	脉冲漏极电流 ⁽¹⁾⁽²⁾	21	A
P_D	功率耗散	500	mW
T_J , T_{stg}	工作结温, 储存温度	-55 至 150	$^\circ\text{C}$
E_{AS}	雪崩能量, 单一脉冲 $I_D = 12.8\text{A}$, $L = 0.1\text{mH}$, $R_G = 25\Omega$	8.2	mJ

(1) $R_{\theta JA} = 245^\circ\text{C/W}$ (典型值)

(2) 脉冲持续时间 $\leq 100\mu\text{s}$, 占空比 $\leq 1\%$ 。

顶视图



目录

1	特性	1	6.1	接收文档更新通知	7
2	应用范围	1	6.2	社区资源	7
3	说明	1	6.3	商标	7
4	修订历史记录	2	6.4	静电放电警告	7
5	Specifications	3	6.5	Glossary	7
	5.1 Electrical Characteristics	3	7	机械、封装和可订购信息	8
	5.2 Thermal Information	3	7.1	机械尺寸	8
	5.3 Typical MOSFET Characteristics	4	7.2	推荐的最小 PCB 布局	9
6	器件和文档支持	7	7.3	推荐的模板布局	9

4 修订历史记录

Changes from Original (May 2016) to Revision A

Page

•	已添加 将 接收文档更新通知 部分添加到 器件和文档支持	7
•	已添加 表 1 添加到了 机械尺寸 部分	8
•	更新了 推荐的最小 PCB 布局	9
•	更新了 推荐的模板布局	9

5 Specifications

5.1 Electrical Characteristics

 $T_A = 25^\circ\text{C}$ (unless otherwise stated)

PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
STATIC CHARACTERISTICS						
BV_{DSS}	Drain-to-source voltage	$V_{GS} = 0\text{ V}, I_{DS} = 250\ \mu\text{A}$	60			V
I_{DSS}	Drain-to-source leakage current	$V_{GS} = 0\text{ V}, V_{DS} = 48\text{ V}$			1	μA
I_{GSS}	Gate-to-source leakage current	$V_{DS} = 0\text{ V}, V_{GS} = 20\text{ V}$			10	μA
$V_{GS(th)}$	Gate-to-source threshold voltage	$V_{DS} = V_{GS}, I_{DS} = 250\ \mu\text{A}$	1.4	1.75	2.2	V
$R_{DS(on)}$	Drain-to-source on-resistance	$V_{GS} = 4.5\text{ V}, I_{DS} = 1\text{ A}$		57	75	m Ω
		$V_{GS} = 10\text{ V}, I_{DS} = 1\text{ A}$		54	65	
g_{fs}	Transconductance	$V_{DS} = 6\text{ V}, I_{DS} = 1\text{ A}$		7.7		S
DYNAMIC CHARACTERISTICS						
C_{iss}	Input capacitance	$V_{GS} = 0\text{ V}, V_{DS} = 30\text{ V},$ $f = 1\text{ MHz}$		598	777	pF
C_{oss}	Output capacitance			47	61	pF
C_{rss}	Reverse transfer capacitance			8.1	10.5	pF
R_G	Series gate resistance			1200	1600	Ω
Q_g	Gate charge total (10 V)	$V_{DS} = 30\text{ V}, I_{DS} = 1\text{ A}$		11	14	nC
Q_{gd}	Gate charge gate-to-drain			1.6		nC
Q_{gs}	Gate charge gate-to-source			1.5		nC
$Q_{g(th)}$	Gate charge at V_{th}			0.8		nC
Q_{oss}	Output charge		$V_{DS} = 30\text{ V}, V_{GS} = 0\text{ V}$		3.2	
$t_{d(on)}$	Turnon delay time	$V_{DS} = 30\text{ V}, V_{GS} = 4.5\text{ V},$ $I_{DS} = 1\text{ A}, R_G = 0\ \Omega$		572		ns
t_r	Rise time			540		ns
$t_{d(off)}$	Turnoff delay time			1076		ns
t_f	Fall time			496		ns
DIODE CHARACTERISTICS						
V_{SD}	Diode forward voltage	$I_{SD} = 1\text{ A}, V_{GS} = 0\text{ V}$		0.8	1	V

5.2 Thermal Information

 $T_A = 25^\circ\text{C}$ (unless otherwise stated)

THERMAL METRIC		MIN	TYP	MAX	UNIT
$R_{\theta JA}$	Junction-to-ambient thermal resistance ⁽¹⁾		85		$^\circ\text{C/W}$
	Junction-to-ambient thermal resistance ⁽²⁾		245		

(1) Device mounted on FR4 material with 1-in² (6.45-cm²), 2-oz (0.071-mm) thick Cu.

(2) Device mounted on FR4 material with minimum Cu mounting area.

5.3 Typical MOSFET Characteristics

T_A = 25°C (unless otherwise stated)

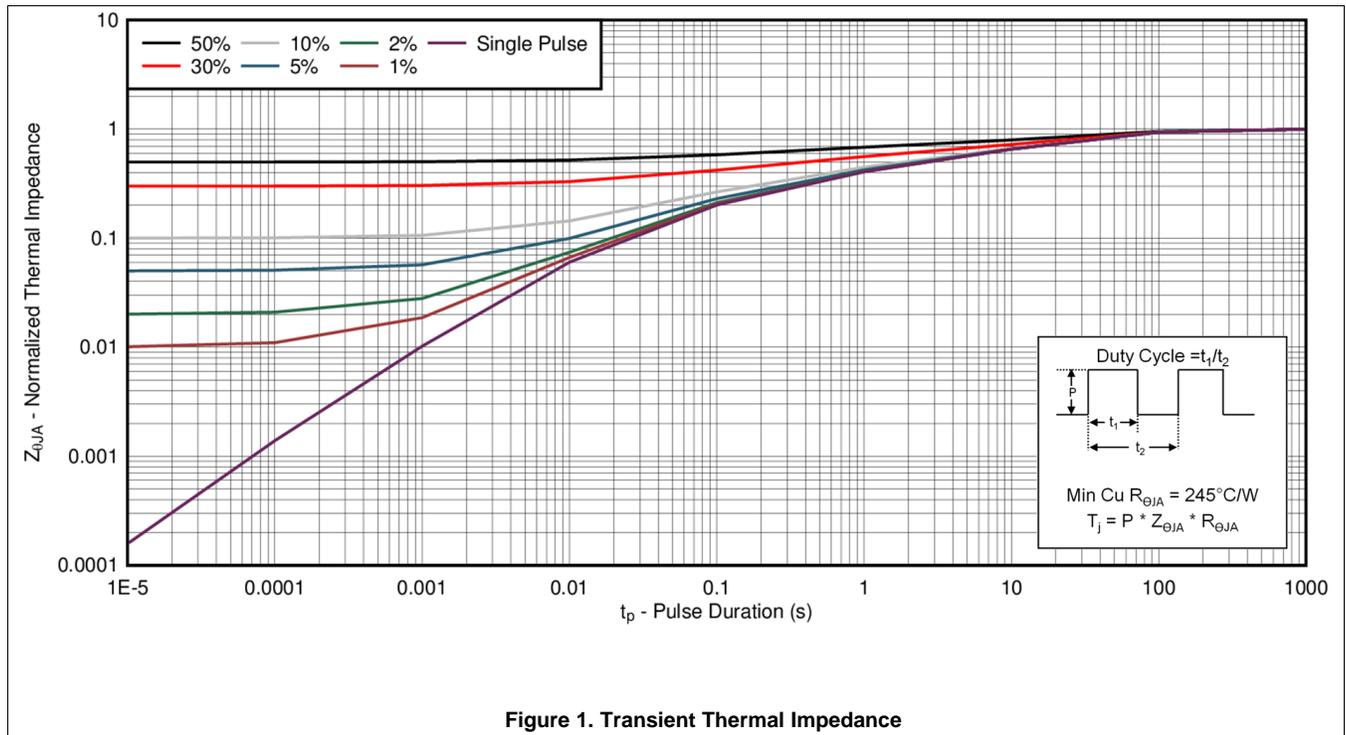


Figure 1. Transient Thermal Impedance

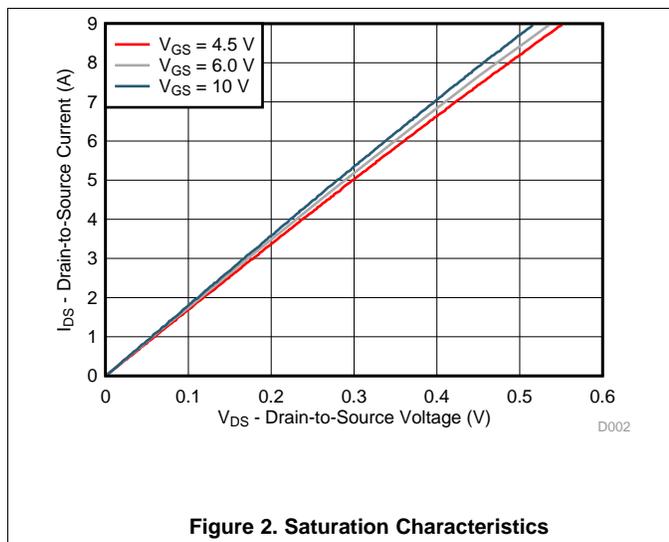


Figure 2. Saturation Characteristics

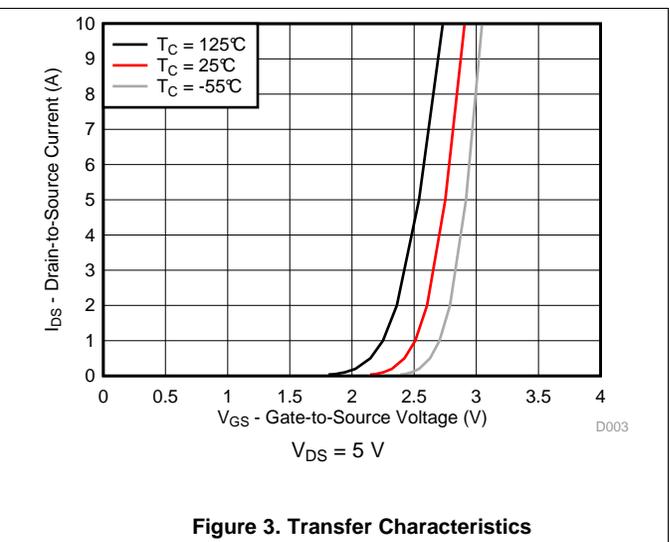
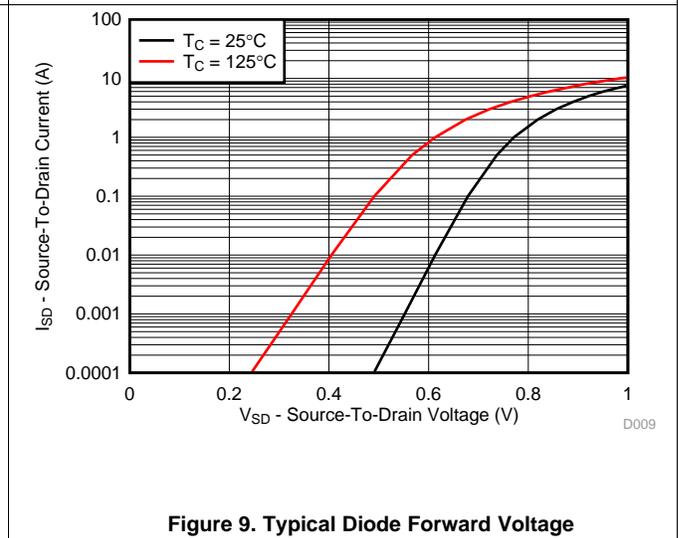
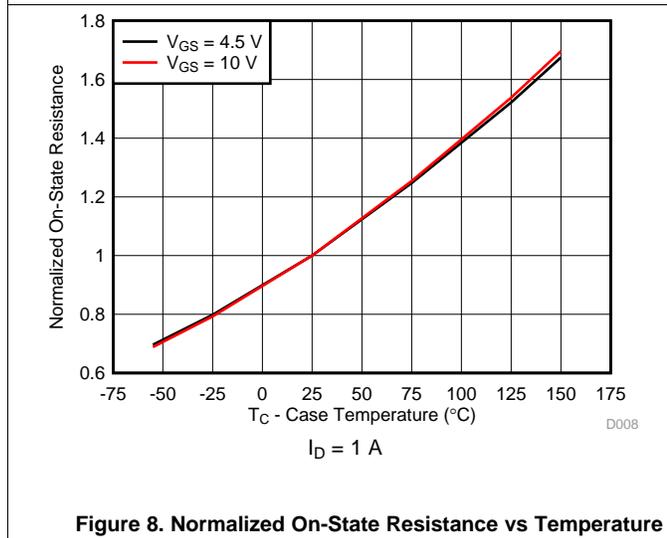
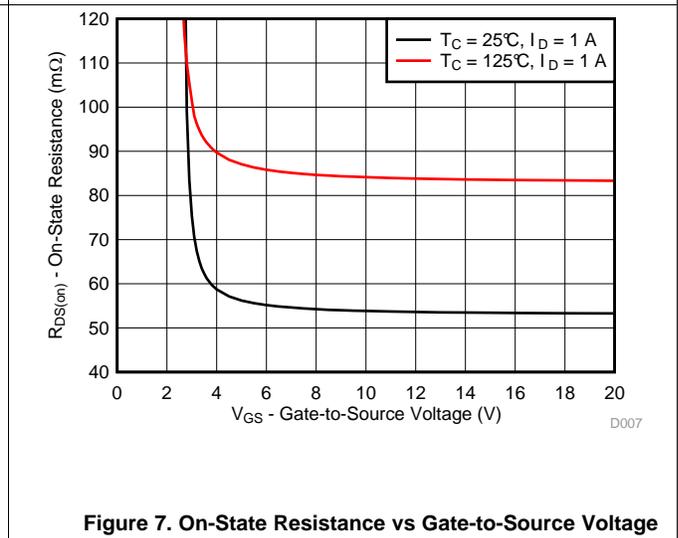
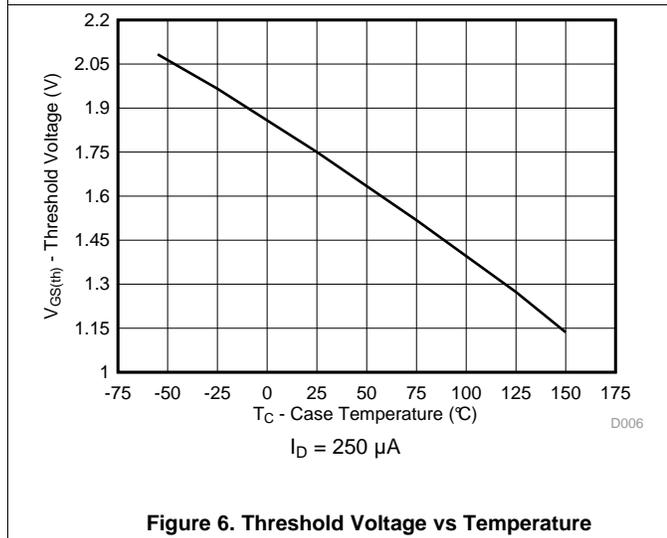
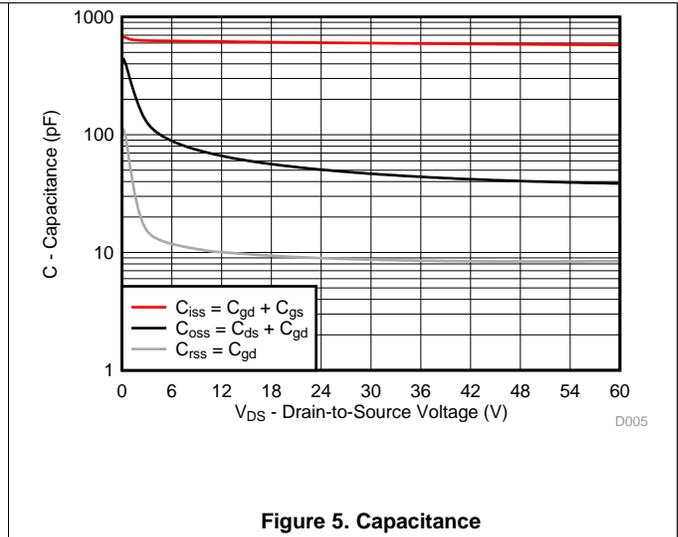
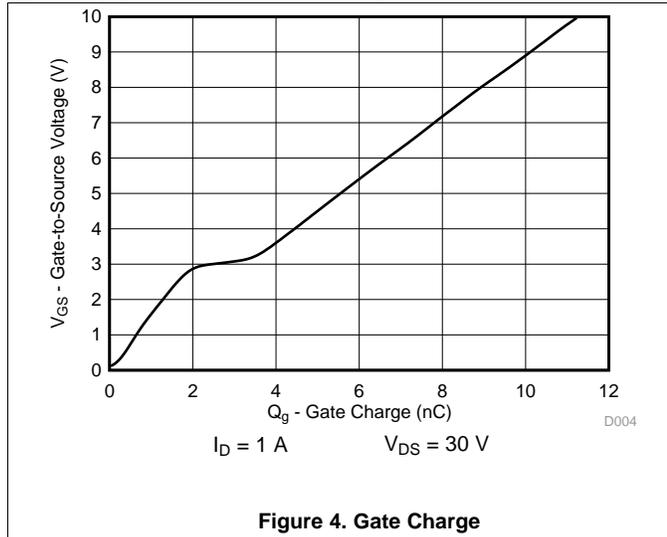


Figure 3. Transfer Characteristics

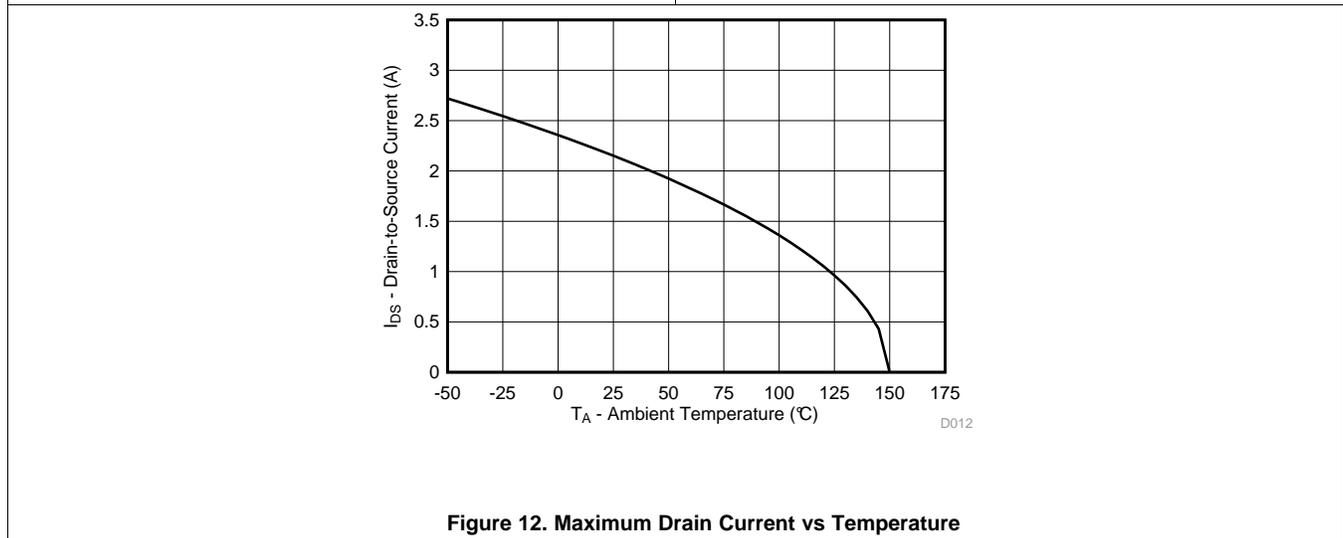
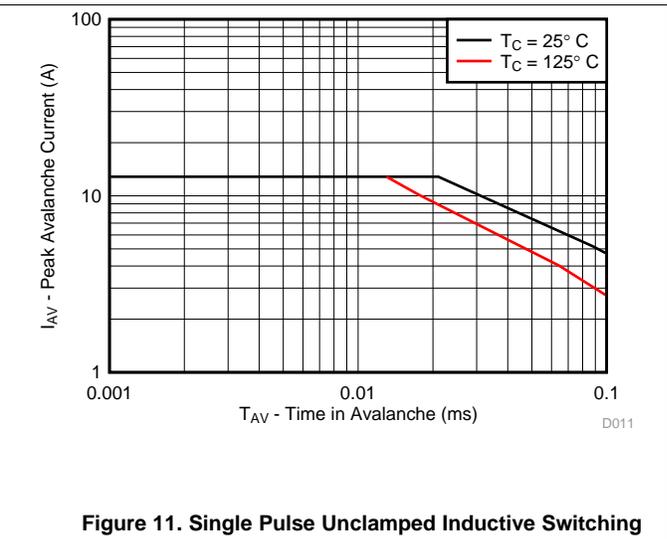
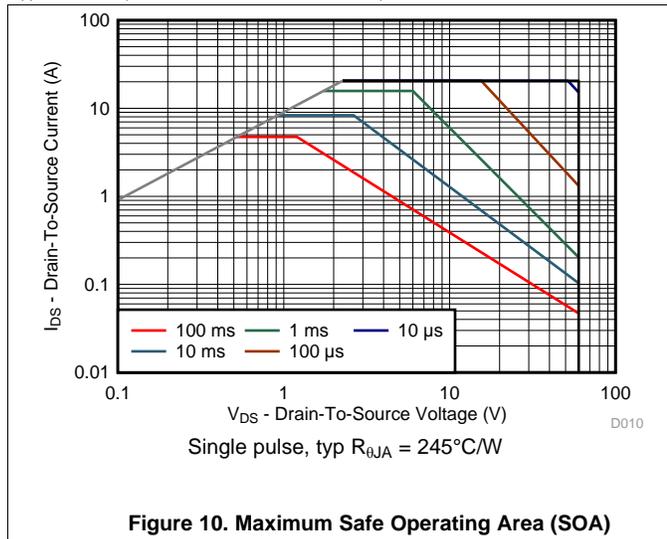
Typical MOSFET Characteristics (continued)

T_A = 25°C (unless otherwise stated)



Typical MOSFET Characteristics (continued)

$T_A = 25^\circ\text{C}$ (unless otherwise stated)



6 器件和文档支持

6.1 接收文档更新通知

要接收文档更新通知，请导航至德州仪器 TI.com.cn 上的器件产品文件夹。请单击右上角的 *通知我* 进行注册，即可收到任意产品信息更改每周摘要。有关更改的详细信息，请查看任意已修订文档中包含的修订历史记录。

6.2 社区资源

下列链接提供到 TI 社区资源的连接。链接的内容由各个分销商“按照原样”提供。这些内容并不构成 TI 技术规范，并且不一定反映 TI 的观点；请参阅 TI 的《使用条款》。

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设计支持 *TI 参考设计支持* 可帮助您快速查找有帮助的 E2E 论坛、设计支持工具以及技术支持的联系信息。

6.3 商标

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All other trademarks are the property of their respective owners.

6.4 静电放电警告



这些装置包含有限的内置 ESD 保护。存储或装卸时，应将导线一起截短或将装置放置于导电泡棉中，以防止 MOS 门极遭受静电损伤。

6.5 Glossary

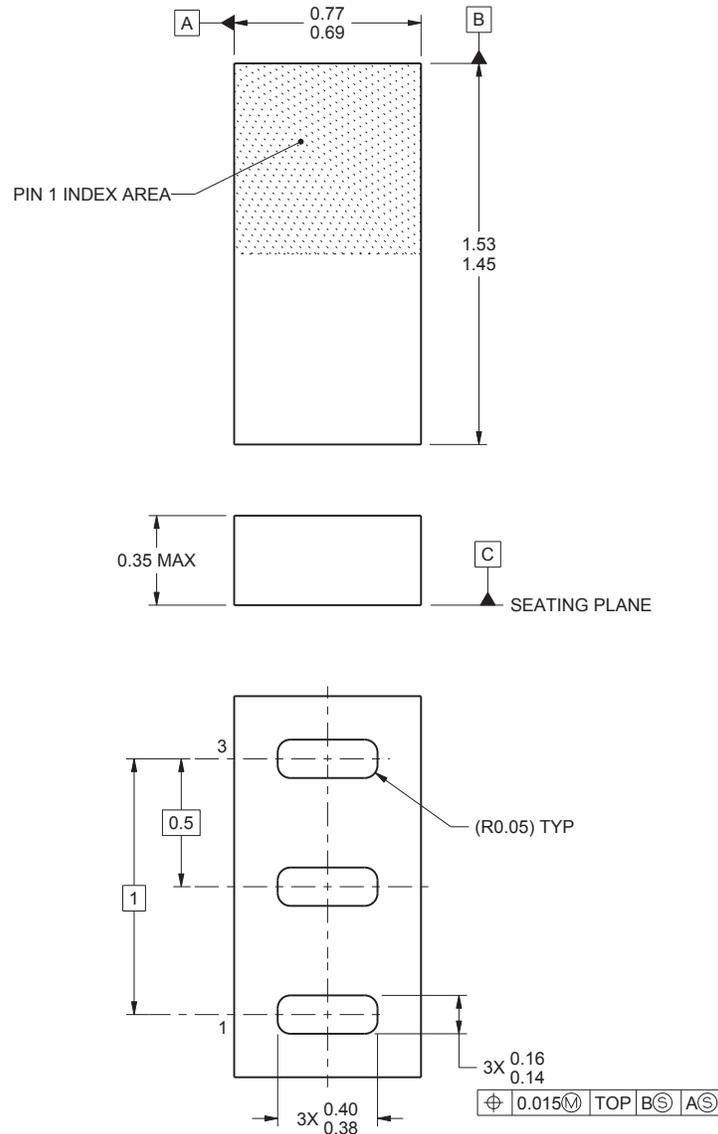
SLYZ022 — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

7 机械、封装和可订购信息

以下页面包括机械、封装和可订购信息。这些信息是指定器件的最新可用数据。这些数据发生变化时，我们可能不会另行通知或修订此文档。如欲获取此产品说明书的浏览器版本，请参阅左侧的导航栏。

7.1 机械尺寸

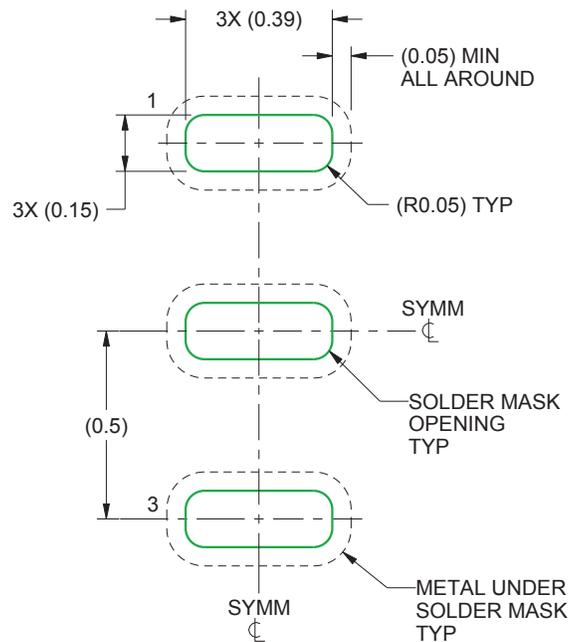


- (1) 所有线性尺寸的单位都是毫米（尺寸和容限值遵循 AME T14.5M-1994）。
- (2) 本图纸如有变更，恕不通知。
- (3) 此封装采用无铅焊盘设计。

将
表 1. 引脚配置

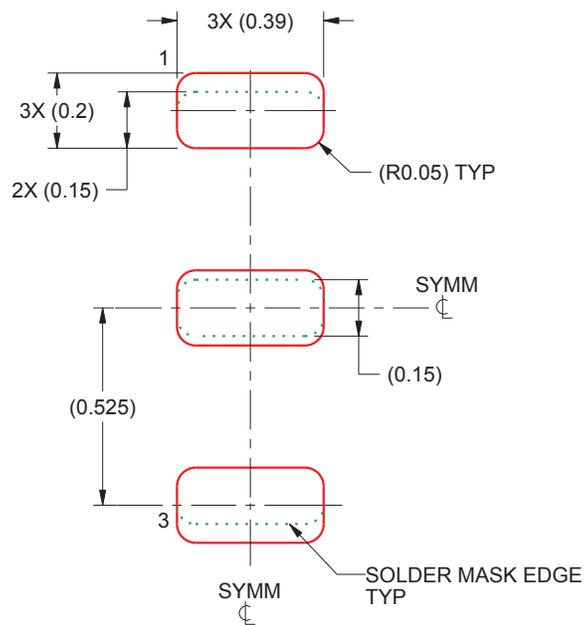
位置	名称
引脚 1	栅极
引脚 2	源极
引脚 3	漏极

7.2 推荐的最小 PCB 布局



(1) 所有尺寸的单位都是毫米。

7.3 推荐的模板布局



(1) 所有尺寸的单位都是毫米。

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
CSD18541F5	ACTIVE	PICOSTAR	YJK	3	3000	RoHS & Green	NIAU	Level-1-260C-UNLIM	-55 to 150	1T	Samples
CSD18541F5T	ACTIVE	PICOSTAR	YJK	3	250	RoHS & Green	NIAU	Level-1-260C-UNLIM	-55 to 150	1T	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBsolete: TI has discontinued the production of the device.

(2) **RoHS:** TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

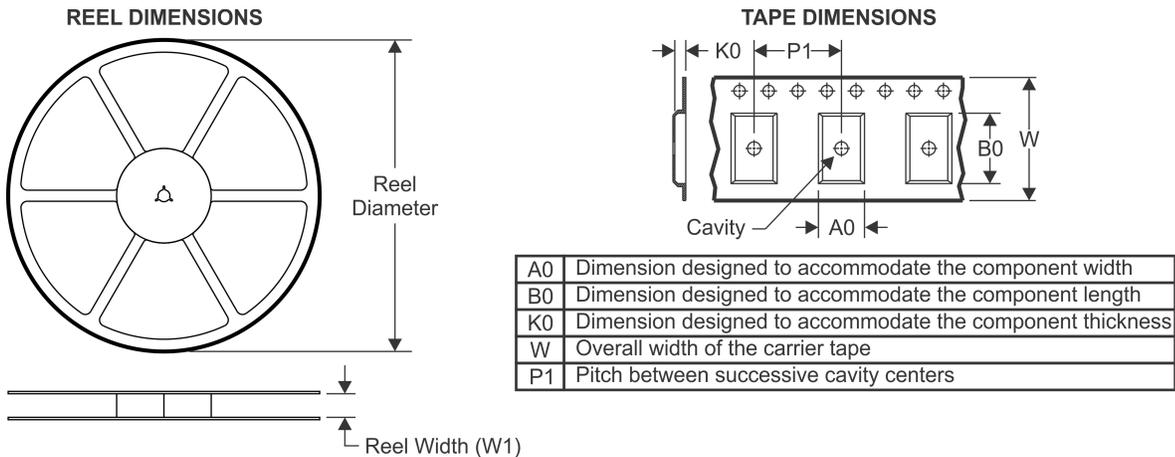
(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

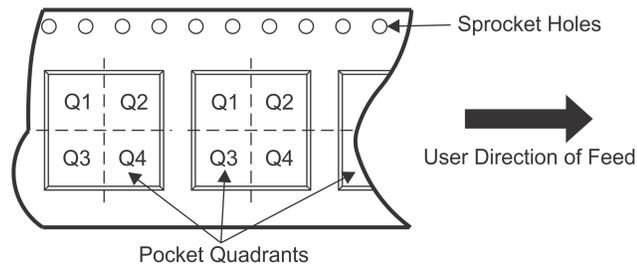
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TAPE AND REEL INFORMATION

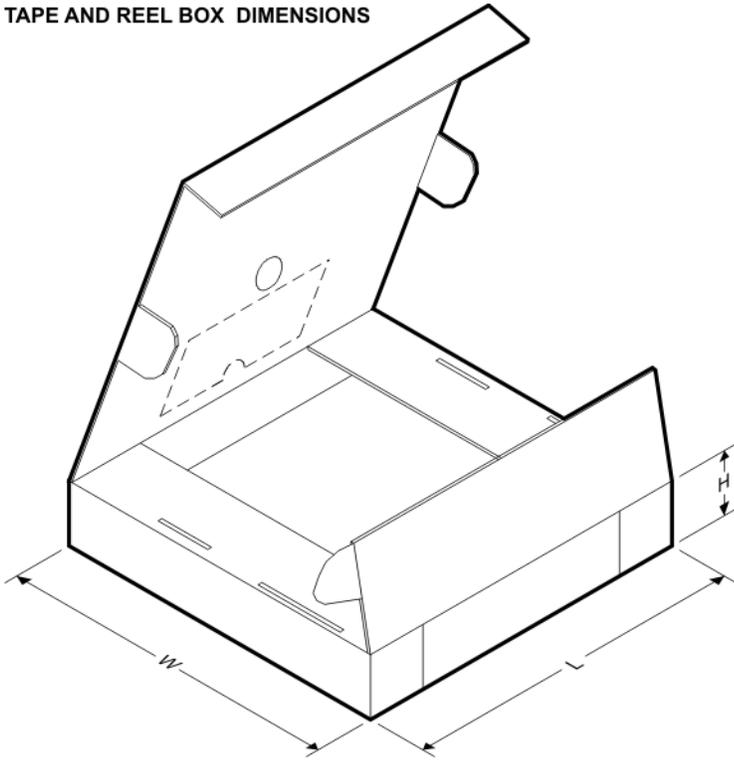


QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	A0 (mm)	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CSD18541F5	PICOST AR	YJK	3	3000	180.0	8.4	0.92	1.68	0.42	4.0	8.0	Q1
CSD18541F5T	PICOST AR	YJK	3	250	180.0	8.4	0.92	1.68	0.42	4.0	8.0	Q1

TAPE AND REEL BOX DIMENSIONS


*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
CSD18541F5	PICOSTAR	YJK	3	3000	182.0	182.0	20.0
CSD18541F5T	PICOSTAR	YJK	3	250	182.0	182.0	20.0

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